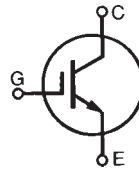


High Current IGBT

Short Circuit SOA Capability

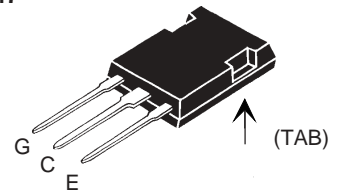
IXSK 80N60B
IXSX 80N60B

$V_{CES} = 600\text{ V}$
 $I_{C25} = 160\text{ A}$
 $V_{CE(sat)} = 2.5\text{ V}$

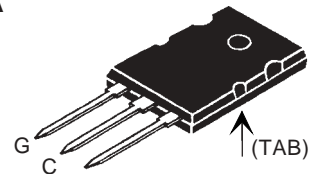


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1\text{ M}\Omega$	600	V
V_{CES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (silicon chip capability)	160	A
I_{C90}	$T_C = 90^\circ\text{C}$ (silicon chip capability)	80	A
$I_{L(RMS)}$	$T_C = 90^\circ\text{C}$ (silicon chip capability)	75	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ ms}$	300	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 5\ \Omega$ Clamped inductive load	$I_{CM} = 160$ @ 0.8 V_{CES}	A
tsc SCSOA	$V_{GE} = 15\text{ V}, V_{CE} = 0.6\text{ V}_{CES}, T_J = 125^\circ\text{C}$ $R_G = 5\ \Omega, \text{non-repetitive}$	10	μs
P_C	$T_C = 25^\circ\text{C}$	500	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	TO-264	0.4/6 Nm/lb.in.
Weight		PLUS 247	6 g
		TO-264	10 g

PLUS 247™ (IXSX)



TO-264 AA (IXSK)



G = Gate
C = Collector

E = Emitter
TAB = Collector

Features

- International standard packages
- Very high current, fast switching IGBT
- Low $V_{CE(sat)}$ - for minimum on-state conduction losses
- MOS Gate turn-on - drive simplicity

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

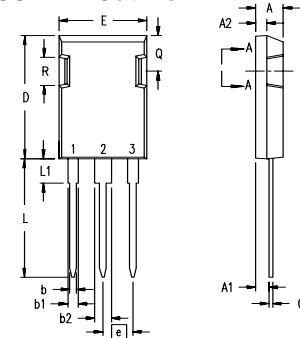
Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 500\ \mu\text{A}, V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 8\text{ mA}, V_{CE} = V_{GE}$	4		V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$			$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$ 200 μA 2 mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 200\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15\text{ V}$			2.5 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	$I_C = 60\text{ A}; V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	52		S	
C_{ies} C_{oes} C_{res}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		6600	pF	
			660	pF	
			196	pF	
Q_g Q_{ge} Q_{gc}	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		240	nC	
			85	nC	
			90	nC	
$t_{d(on)}$ t_{ri} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 2.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		60	ns	
			45	ns	
			140	280	ns
			180	280	ns
			4.2	7.0	mJ
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 2.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		60	ns	
			60	ns	
			4.8		mJ
			190		ns
			260		ns
			6.7		mJ
R_{thJC} R_{thCK}			0.26	KW	
		0.15		KW	

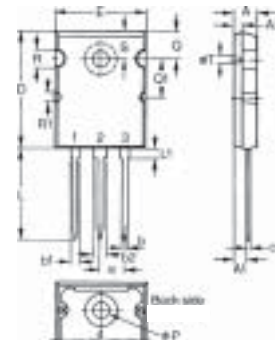
PLUS 247™ Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L ₁	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A ₁	2.54	2.89	.100	.114
A ₂	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b ₁	2.39	2.69	.094	.106
b ₂	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L ₁	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q ₁	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R ₁	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	